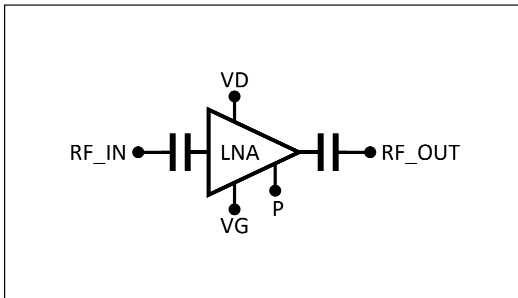
Product Overview

The ASL6013 is a GaN PHEMT MMIC Low Noise Amplifier (LNA) chip which operates from 8.5 to 12 GHz. The ASL6013 features extremely flat performance characteristics including 12 dB of small signal gain, 1.9 dB of noise figure, output IP3 of +36 dBm and output P1dB of +28 dBm across the operating band. The ASL6013 has a power handling capacity of 6.5 W continues wave (CW) with a recovery time of 1 us. This versatile LNA is ideal for hybrid and MCM assemblies due to its compact size, consistent output power and DC blocked RF I/O's. All data is measured with the chip in a 50 Ohm test fixture connected via two 0.025 mm (1 mil) diameter bond wires of minimal length 0.51 mm (20 mil).

Key Features

1. Fully integrated, high performance LNA
2. Integrated DC blocking at RF output
3. Bandwidth: 8.5 GHz to 12 GHz
4. Power Gain : 12 dB
5. Low Noise Figure: 1.9 dB
6. Output P1dB: +28 dBm
7. Power Handling: 6.5 dBm (CW), 13 dBm (Pulsed)
8. 50 Ohm Matched Input/output
9. Die Size: 2.85 x 1.85 x 0.1 mm

Functional Block Diagram



Applications

1. Instrumentation
2. Point-to-point communication

Absolute Maximum Rating

Drain Bias Voltage (VDD)	+40 Vdc
Gate Bias Voltage (VG1,G2)	-25 Vdc
RF Input Power (CW)(VDD = +10 Vdc)	37.5 dBm
RF Input Power (Pulsed)(VDD = +10 Vdc)	40.5 dBm
Channel Temperature	200 °C
Continuous Pdiss(T = 85 °C)	0.55 W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +65 °C
Thermal Resistance (channel to ground pad)	55 °C/W

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

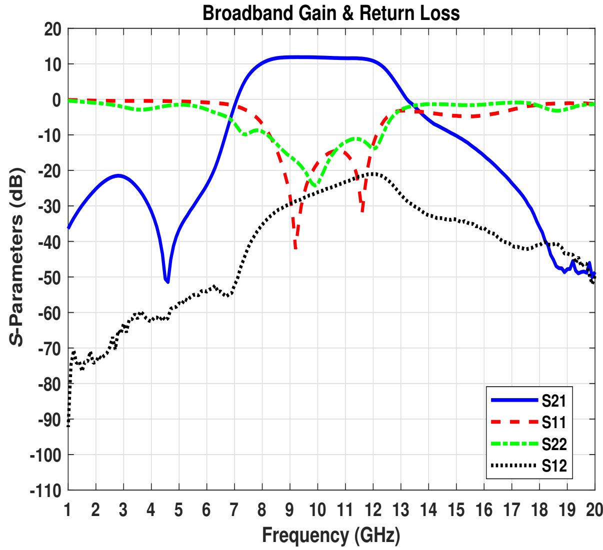
Electrical Specifications

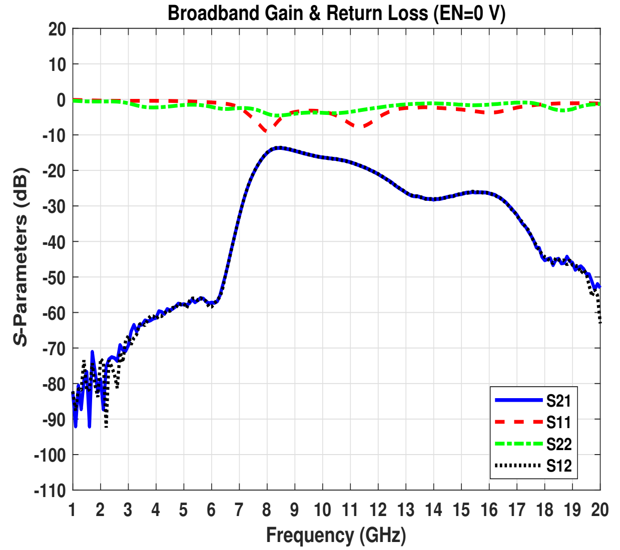
Parameter	Min.	Typ.	Max.	Units
Frequency Range	8.5	-	12	GHz
Gain	12	15.2	-	dB
Noise Figure	-	1.9	3	dB
Input Return Loss	10	15	-	dB
Output Return Loss	10	15	-	dB
Output Power for 1 dB Compression (P1dB)	-	28	-	dBm
Saturated Output Power	-	33	-	dBm
Output Third Order Intercept Point (OIP3)	-	36	-	dBm
Supply Current	-	280	-	mA

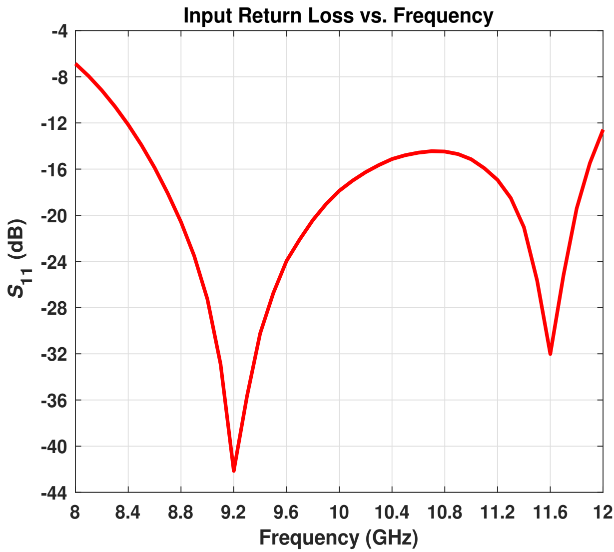
Test conditions unless otherwise noted:TA=+25 °C, VDD=10 V, VSS=-3.1 V, Vp=-5 V, ID=280 mA, Z0=50 Ω

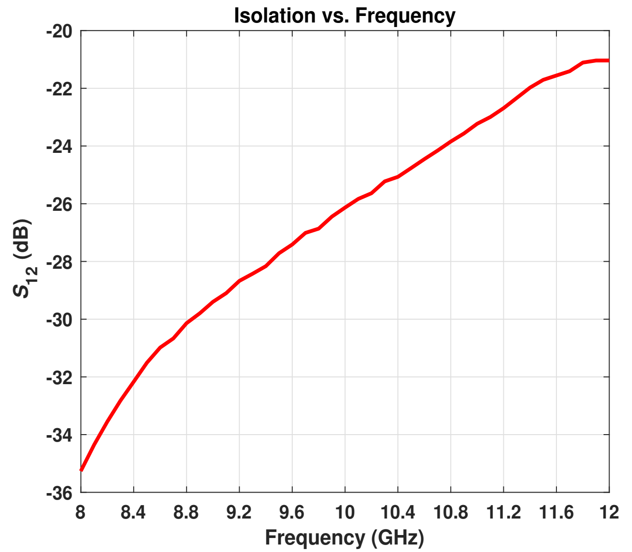
Typical Performance Curves

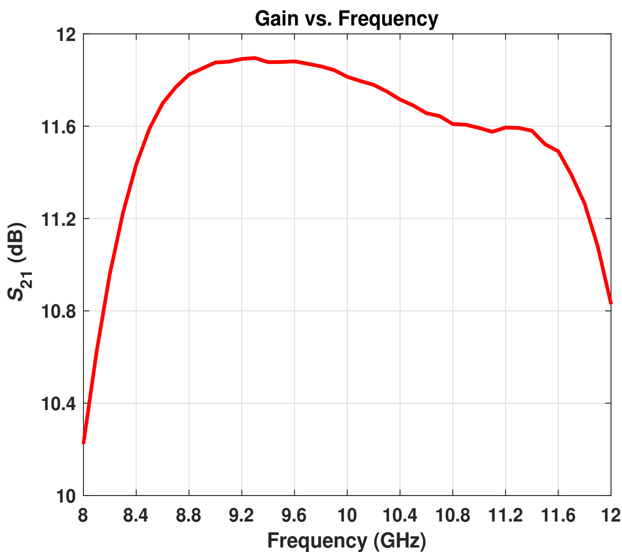
Test conditions unless otherwise noted:VDD=10 V, VG1,2=-3.1 V,P=-5 V, IDQ=280 mA

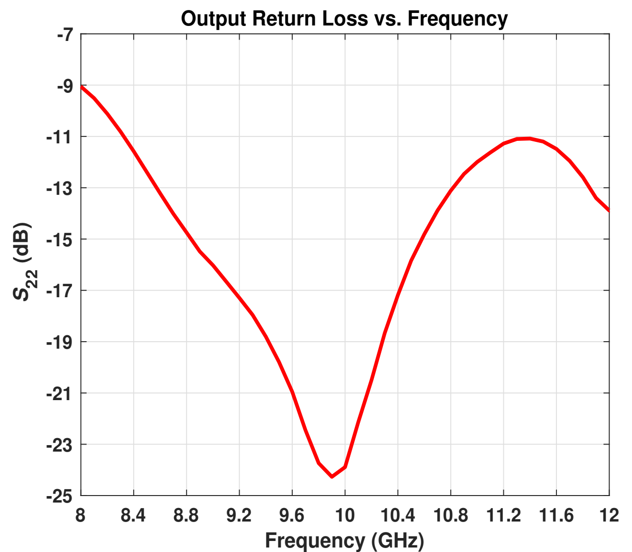






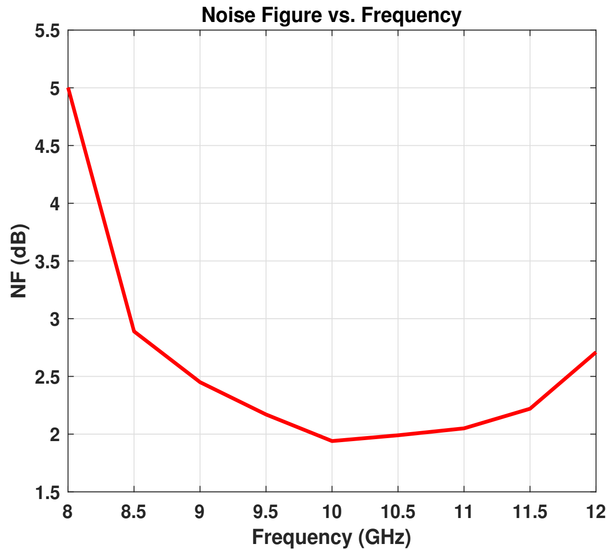


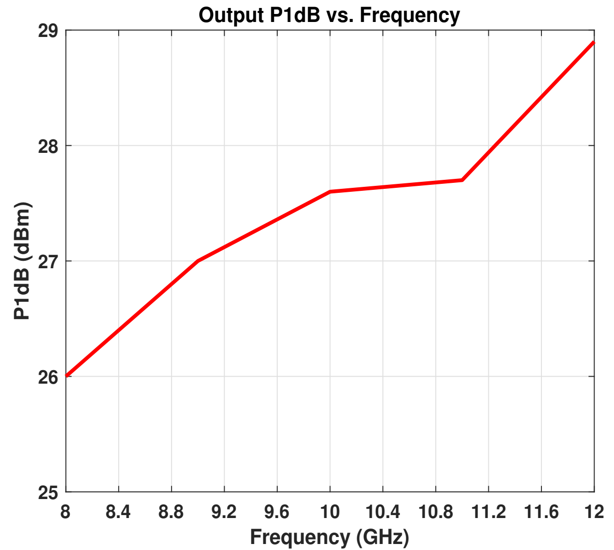


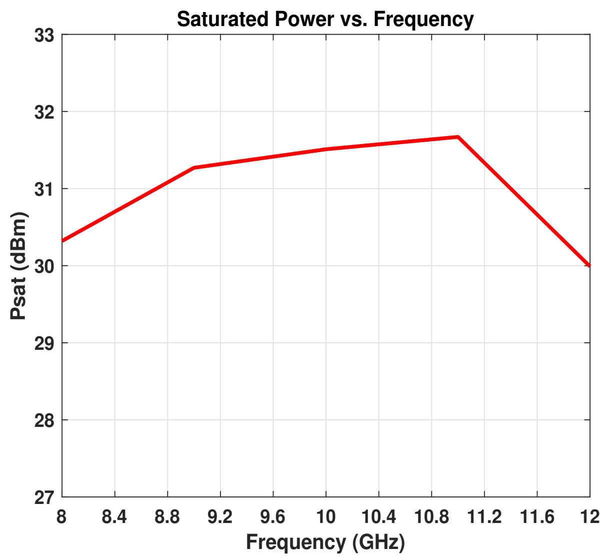


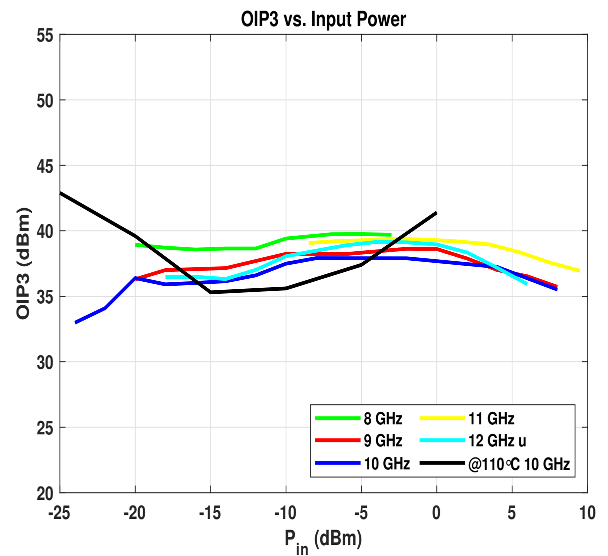
Typical Performance Curves

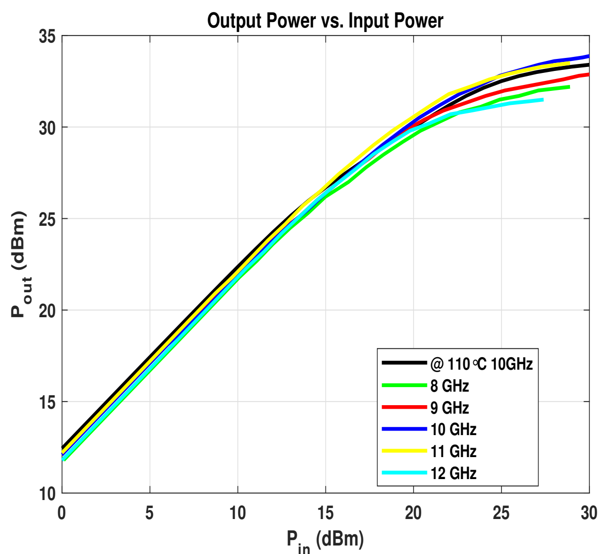
Test conditions unless otherwise noted:VDD=10 V, VG1,2=-3.1 V, P=-5 V, IDQ=280 mA

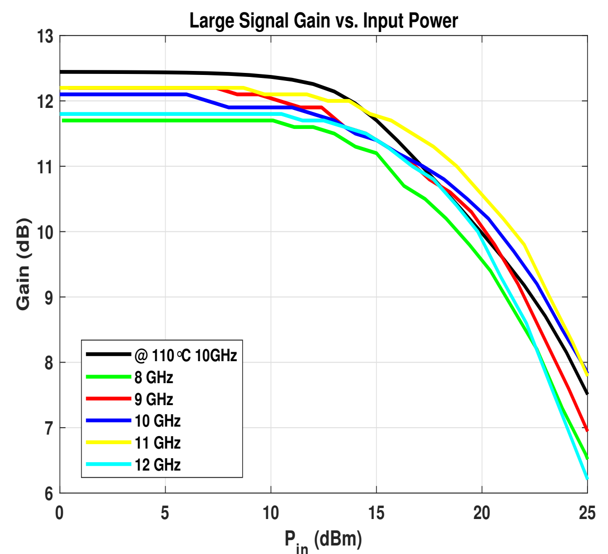




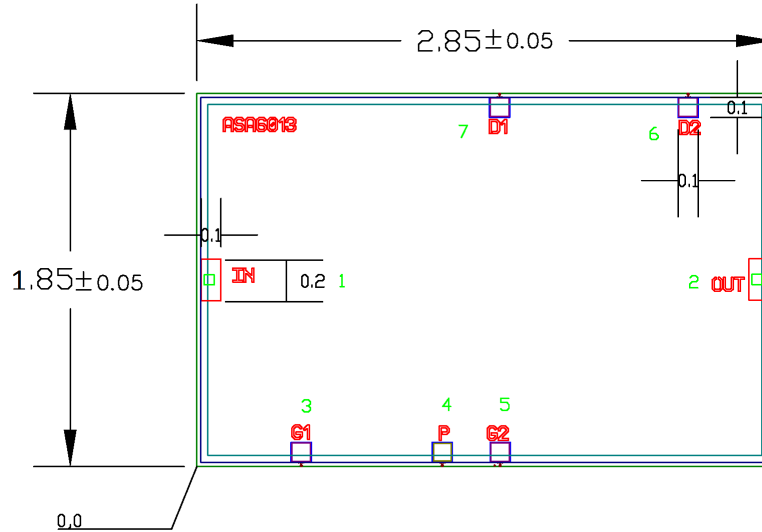








Mechanical Information



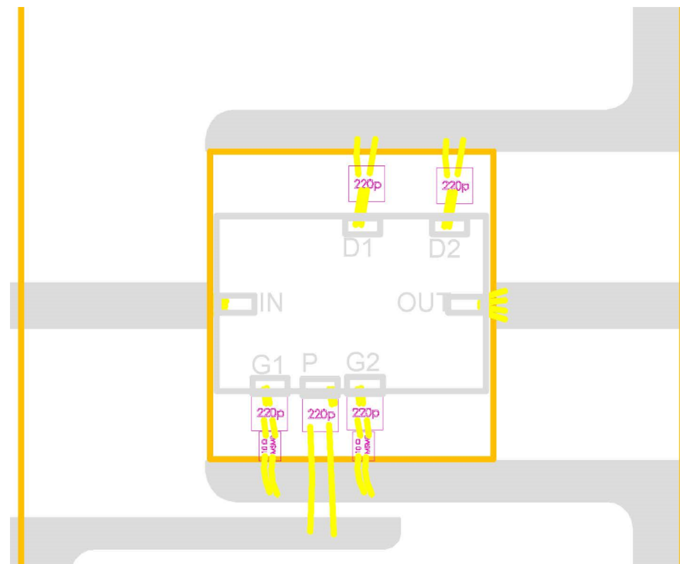
NOTES:

1. ALL DIMENSIONS IN MILLIMETERS
2. DIE THICKNESS IS 100 µm
3. TYPICAL BOND PAD IS 0.01 mm2
4. BACKSIDE METALLIZATION: GOLD
5. BACKSIDE METAL IS GROUND
6. BOND PAD METALLIZATION: GOLD
7. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
8. Die Size: OVERALL DIE SIZE ±50 µm

Bond Pad Description

1	RF-IN	This pad is AC coupled and matched to 50 Ohms.
2	RF-OUT	This pad is AC coupled and matched to 50 Ohms.
3,5	VG1,2	Negative Supply Voltage for the amplifier.External bypass capacitors of 220 pF are optional.
4	P	Protection Pad
6,7	VD1,2	Positive Supply Voltage for the amplifier. External bypass capacitors of 220 pF are optional.

Assembly Diagram



Assembly Notes

Component Placement and Adhesive Attachment Assembly Notes:

1. Use vacuum collet to pick up the die.
2. The force should be controlled during placement and mounting specially no force should be applied to air bridges.

Reflow process assembly notes:

1. Use CMC or MoCu carrier to decrease thermal expansion mechanical stress
2. Use AuSn (80/20) solder and limit exposure to temperatures above 300 °C to 3-4 minutes, maximum.
3. An alloy station or conveyor furnace with reducing atmosphere should be used.
4. Do not use any kind of flux.
5. Devices must be stored in a dry nitrogen atmosphere.
6. Use Au bond wire.

Contact Information

For the latest specifications, additional product information:
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